

## **ABSTRACT OF THE DISCLOSURE**

A shielding film having a higher lead content than that of a capacitive insulating film is formed under a lower electrode of a capacitor in a FeRAM memory cell, and another shielding film having a higher lead content than that of the capacitive insulating film is formed on an upper electrode. PZT films to be used as barrier layers are formed in the interlayer insulating films of the FeRAM memory cell. As a result, it is possible to prevent H<sub>2</sub> or H<sub>2</sub>O from entering an upper portion or a lower portion of the capacitor, and lead diffused from the capacitive insulating film can be compensated by lead included in the shielding films, and it is possible to prevent characteristics of the capacitive insulating film from being degraded.